

AMENDMENTS TO THE CLAIMS

1. (Currently Amended): A light emitting device comprising:

a thin film transistor (TFT) on an insulating base material; and
above the TFT,
a luminous section including a luminous material layer; and
electrode layers supplying current to the luminous material layer; and
a plurality of openings intermittently spaced in one pixel in a predetermined pattern on one of the insulating base material and at least one material placed above the insulating base material and below the luminous material layer.

2. (Currently Amended): A light emitting device comprising[[,]]:

stacked above an insulating base material,
a first electrode layer to supply current to a luminous material layer, the luminous material layer emitting light by supplying current thereto, and
a second electrode layer to supply current to the luminous material layer;
either the first electrode layer or the second electrode layer being made of a transparent material; and
a plurality of intermittently spaced openings in a predetermined pattern on either the first electrode layer or second electrode layer made of the transparent material, and concavities and convexities formed on the luminous material layer and on the other electrode layer.

3. (Previously presented): A light emitting device comprising:

stacked above an insulating base material,
at least a first electrode layer to supply current to a luminous material layer,
the luminous material layer emitting light by supplying current thereto, and
a second electrode layer to supply current to the luminous material layer;
either the first electrode layer or the second electrode layer being made of a
transparent material; and
either the first electrode layer or the second electrode layer made of the
transparent material in plan view has a comb shape partly having circular regions,
and the luminous material layer and the other electrode layer stacked on the
electrode layer made of the transparent material are in the shape of concavities and
convexities in side view.

4. (Currently amended): A light emitting device comprising:

a TFT ~~fabricated~~ on an insulating base material; and
stacked above the [[TFT]]insulating base material,
at least an insulating layer, a first electrode layer to supply current to a
luminous material layer, the luminous material layer emitting light by supplying
current thereto, and a second electrode layer to supply current to the luminous
material layer;
the first electrode layer being made of a transparent material;

the second electrode layer being made of a reflecting material;
a plurality of openings intermittently spaced in one pixel on one of the insulating base material and at least one material placed above the insulating base material and below the luminous material layer; and
the first electrode layer on convex sections of the insulating layer.

5. (Currently amended): A light emitting device comprising:

a TFT on an insulating base material; and
stacked above the [[TFT]] insulating base material,
at least an insulating layer, a first electrode layer to supply current to a luminous material layer, the luminous material layer emitting light by supplying current thereto, and a second electrode layer to supply current to the luminous material layer;
the second electrode layer being made of a transparent material;
the first electrode layer being made of a reflecting material;
a plurality of intermittently spaced openings in a predetermined pattern on at least one of the insulating base material and at least one material placed above the insulating base material and below the luminous material layer; and
the second electrode layer is on concave sections of the luminous material layer.

6. (Original): The light emitting device as claimed in claim 1, wherein the luminous material layer is made of organic materials.

7. (Original): The light emitting device as claimed in claim 2, wherein the luminous material layer is made of organic materials.

8. (Original): The light emitting device as claimed in claim 3, wherein the luminous material layer is made of organic materials.

9. (Original): The light emitting device as claimed in claim 4, wherein the luminous material layer is made of organic materials.

10. (Original): The light emitting device as claimed in claim 5, wherein the luminous material layer is made of organic materials.

11. (Previously presented): The light emitting device as claimed in claim 2, wherein:

the luminous material layer is made of inorganic materials; further comprising

a first insulating layer between the luminous material layer and the first electrode layer; and

a second insulating layer between the luminous material layer and the second electrode layer.

12. (Previously presented): The light emitting device as claimed in claim 3, wherein:

the luminous material layer is made of inorganic materials; further
comprising

a first insulating layer between the luminous material layer and the first
electrode layer; and

a second insulating layer between the luminous material layer and the
second electrode layer.

13. (Previously presented): The light emitting device as claimed in claim 4,
wherein:

the luminous material layer is made of inorganic materials; further
comprising

a first insulating layer between the luminous material layer and the first
electrode layer; and

a second insulating layer between the luminous material layer and the
second electrode layer.

14. (Previously presented): The light emitting device as claimed in claim 5,
wherein:

the luminous material layer is made of inorganic materials; further
comprising

a first insulating layer between the luminous material layer and the first
electrode layer; and

a second insulating layer between the luminous material layer and the

second electrode layer.

15. (Currently Amended): A production method of a light emitting device formed through a thin film transistor (TFT) fabrication process fabricating a TFT on an insulating base material and a luminous section fabrication process fabricating a luminous section including a luminous material layer and electrode layers supplying current to the luminous material layer above the TFT, comprising a process of developing a plurality of intermittently spaced openings in a predetermined pattern to at least one of the insulating base material and at least one material placed above the insulating base material and below the luminous material layer in the TFT fabrication process or the luminous section fabrication process.

16. (Currently Amended): A production method of a light emitting device comprising steps of:

forming a first electrode layer to supply current to a luminous material layer above an insulating base material;

forming the luminous material layer emitting light by supplying current thereto on the first electrode layer; and

forming a second electrode layer to supply current to the luminous material layer on the luminous material layer, wherein:

at least one of the first electrode layer and the second electrode layer is made of a transparent material; and

a plurality of intermittently spaced openings are developed in a predetermined pattern to the electrode layer made of the transparent material, and concavities and convexities are formed to the luminous material layer and the other electrode layer owing to the plurality of openings.

17. (Previously presented): A production method of a light emitting device comprising steps of;

forming a first electrode layer to supply current to a luminous material layer above an insulating base material;

forming the luminous material layer emitting light by supplying current thereto on the first electrode layer; and

forming a second electrode layer to supply current to the luminous material layer on the luminous material layer, wherein:

at least one of the first electrode layer and the second electrode layer is made of a transparent material; and

the electrode layer made of the transparent material has a comb shape in plan view, and the luminous material layer and the other electrode layer stacked on the electrode layer made of the transparent material are formed in the shape of concavities and convexities in side view.

18. (Currently Amended): A production method of a light emitting device comprising steps of:

fabricating a TFT on an insulating base material;

forming an insulating layer above the insulating base material on which the TFT is fabricated;

forming a first electrode layer to supply current to a luminous material layer on the insulating layer;

forming the luminous material layer emitting light by supplying current thereto on the first electrode layer; and

forming a second electrode layer to supply current to the luminous material layer on the luminous material layer, wherein:

the first electrode layer is made of a transparent material;

the second electrode layer is made of a reflecting material;

a plurality of intermittently spaced openings are formed to at least one of the insulating base material and at least one material placed above the insulating base material and below the luminous material layer in the TFT fabrication process or the insulating layer forming process; and

the first electrode layer is formed on convex sections of the insulating layer formed owing to the plurality of openings.

19. (Currently Amended): A production method of a light emitting device comprising steps of:

fabricating a TFT on an insulating base material;

forming an insulating layer above the insulating base material on which the TFT is fabricated;

forming a first electrode layer to supply current to a luminous material layer on the insulating layer;

forming the luminous material layer emitting light by supplying current thereto on the first electrode layer; and

forming a second electrode layer to supply current to the luminous material layer on the luminous material layer, wherein:

the second electrode layer is made of a transparent material;

the first electrode layer is made of a reflecting material;

a plurality of intermittently spaced openings are formed in a predetermined pattern to at least one of the insulating base material and at least one material placed above the insulating base material and below the luminous material layer in the TFT fabrication process or the insulating layer forming process; and

the second electrode layer is formed on concave sections of the luminous material layer formed owing to the plurality of openings.